

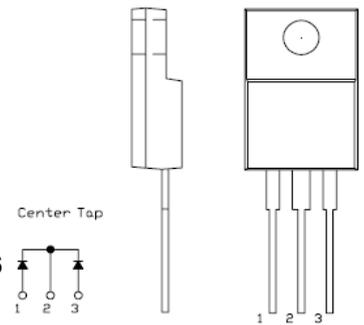
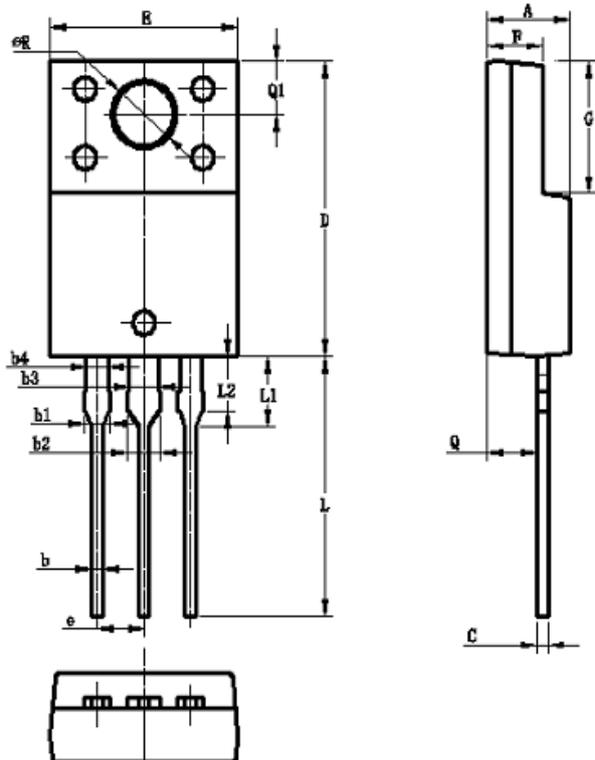
MBRF2060CTL SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

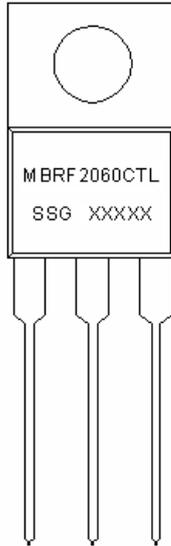
Features:

- 125 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals: pure tin plated, solderable per MIL-STD-750, Method 2026
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request


OUTLINE DRAWING
Mechanical Dimensions: In mm


Dim	OPTION 1(CJ)		OPTION 2(HD)	
	Min	Max	Min	Max
A	4.4	4.6	4.30	4.70
b	0.6TYP		0.50	0.75
b1	1.3TYP		1.30	1.40
b2	1.7TYP		1.70	1.80
b3	1.6TYP		1.50	1.75
b4	1.2TYP		1.10	1.35
C	0.60TYP		0.50	0.75
D	14.8	15.1	14.80	15.20
E	10.06	10.26	9.96	10.36
e	2.55TYP		2.54TYP	
F	2.9	3.1	2.80	3.20
G	6.5	6.9	6.50	6.90
L	12.7	13.7	12.8	13.2
L1	3.4	3.8	3.60	4.00
L2	2.6	3.0	-	-
Q	2.5	2.9	2.50	2.90
Q1	2.5	2.9	2.70REF	
ØR	3.5REF		3.50REF	

ITO-220AB

Marking Diagram:


Where XXXXX is YYWWL

MBR	= Device Type
F	= Package Type
20	= Forward Current (20A)
60	= Reverse Voltage (60V)
CTL	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRF2060CTL	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

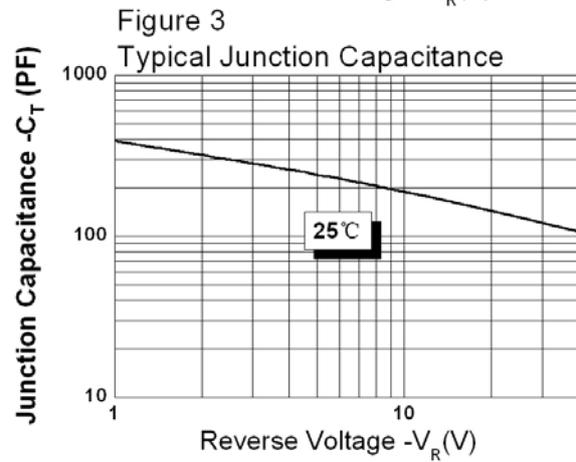
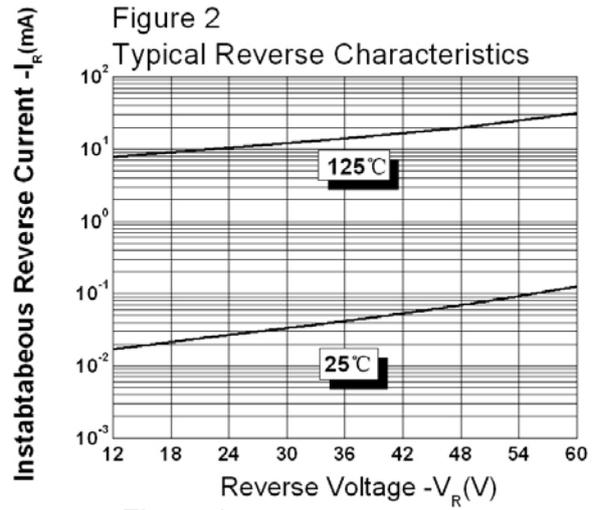
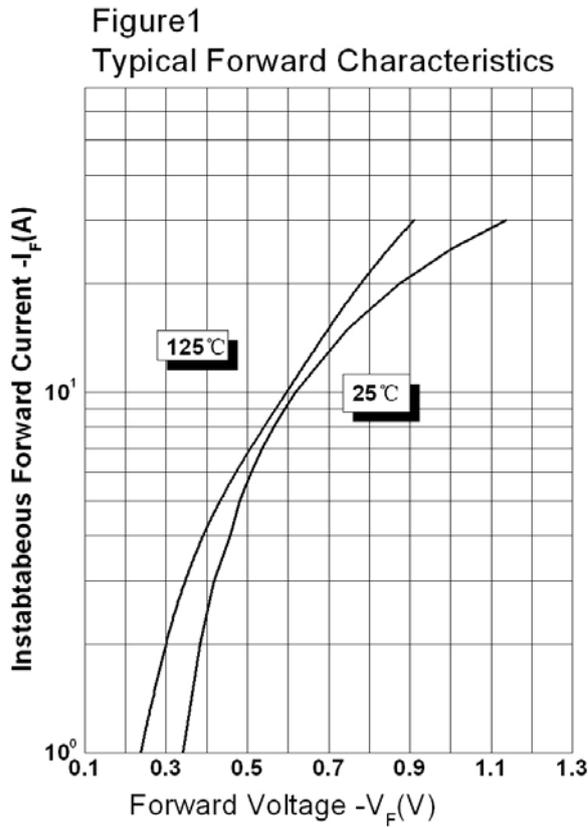
Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	60	V
Average Rectified Output Current(per device)	I_o	50% duty cycle @ $T_C=80^\circ\text{C}$, rectangular wave form	20	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	150	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.62	0.69	V
Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ Pulse $T_J = 25\text{ }^\circ\text{C}$	0.15	1.0	mA
Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	250	400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	2.3	$^\circ\text{C/W}$
Typical Thermal Resistance Case to Heat Sink	$R_{\theta CS}$	Mounting surface, smooth and greased (only for TO-220)	0.50	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			





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